NPN SILICON HIGH FREQUENCY TRANSISTOR

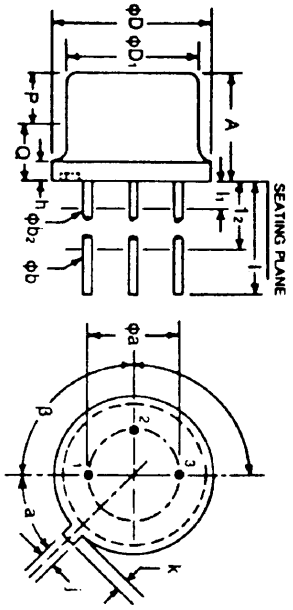
DESCRIPTION:

The **TP2314A** is a High Frequency Transistor Designed for Large Signal Power Amplifier Applications,With Emitter Grounded to Case.

MAXIMUM RATINGS

I	400 mA
V	16 V
P_{DISS}	5.0 W @ T_C = 25 ^{O}C
T_J	-65 ^{O}C to +200 ^{O}C
T_{STG}	-65 ^{O}C to +200 ^{O}C
θ_{JC}	35 ^{O}C/W

PACKAGE STYLE TO-39 (CE)



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
Φa	0.190	0.210	4.83	5.33
A	0.240	0.260	6.10	6.60
Φb	0.016	0.021	0.406	0.533
Φb2	0.016	0.019	0.406	0.483
ΦD	0.350	0.370	8.89	9.40
ΦD1	0.315	0.335	8.00	8.51
h	0.009	0.125	0.229	3.18
j	0.028	0.034	0.711	0.864
k	0.029	0.040	0.737	1.02
l	0.500		12.70	
l1		0.050		1.27
l2	0.250		6.35	
P	0.100		2.54	
Q				
a	45° NOMINAL			
β	90° NOMINAL			

1 = COLLECTOR 2 = BASE
3 = EMITTER

CHARACTERISTICS T_C = 25 ^{O}C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I_C = 50 mA	16			**V**
BV_{CES}	I_C = 50 mA	36			**V**
BV_{CBO}	I_C = 50 mA	36			**V**
I_{CBO}	V_{CB} = 15 V			1.0	**mA**
BV_{EBO}	I_E = 1.0 mA	4.0			**V**
h_{FE}	V_{CE} = 5.0 V I_C = 50 mA	20		200	**---**
C_{ob}	V_{CB} = 12.5 V f = 1.0 MHz			15	**pF**
G_{PE}	V_{CC} = 6.0 V P_{out} = 1.0 W f = 175 MHz	6.0			**dB**
η			50		**%**

Specifications are subject to change without notice.